



# PST KP2000-52

## HIGH POWER PHASE CONTROL THYRISTOR FOR PHASE CONTROL APPLICATIONS

### Features :

- Blocking Capability up to 5200 V
- High dV/dt Capability
- All Diffused Structure
- Amplifying Gate Configuration
- Rugged Ceramic Hermetic Package

### ELECTRICAL CHARACTERISTICS AND RATINGS

#### Blocking

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Repetitive peak reverse voltage	$V_{RRM}$		5200		V	$T_j = -40^\circ C$ to $125^\circ C$
Repetitive peak off-state voltage	$V_{DRM}$		5200		V	$T_j = -40^\circ C$ to $125^\circ C$
Non repetitive peak reverse voltage	$V_{RSM}$		5300		V	$T_j = -40^\circ C$ to $125^\circ C$
Repetitive peak reverse current	$I_{RRM}$		200		mA	$T_j = T_{jmax}$ , $V = V_{RRM}$
Repetitive peak off-state current	$I_{DRM}$		200		mA	$T_j = T_{jmax}$ , $V = V_{DRM}$

#### Conducting

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Average value of on-state current	$I_{T(AV)}$		2330		A	50 Hz sine wave, $180^\circ$ conduction, $T_c = 85^\circ C$
RMS value of on-state current	$I_{T(RMS)}$		3658		A	50 Hz sine wave, $180^\circ$ conduction, $T_c = 85^\circ C$
Surge non repetitive current	$I_{TSM}$		42		kA	50 Hz sine wave Half cycle
$I^2 t$	$I^2 t$		8820		kA <sup>2</sup> s	$V_R = 0$ $T_j = 125^\circ C$
Peak on-state voltage	$V_{TM}$		1.58		V	On-state current 2000 A, $T_j = T_{jmax}$
Threshold voltage	$V_{T(TO)}$		1.02		V	$T_j = T_{jmax}$
On-state slope resistance	$r_T$		0.280		mΩ	$T_j = T_{jmax}$
Holding current	$I_H$			300	mA	$V_D = 24 V$ ; $I_T = 2.5 A$
Latching current	$I_L$			1500	mA	$V_D = 24 V$ ; $R_L = 12 \Omega$

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### Triggering

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Gate current	$I_{GT}$		500		mA	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = -40 \text{ }^\circ\text{C}$
			300		mA	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = 25 \text{ }^\circ\text{C}$
			200		mA	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = 125 \text{ }^\circ\text{C}$
Gate voltage	$V_{GT}$		5		V	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = -40 \text{ }^\circ\text{C}$
			3		V	$V_D = 6 \text{ V}; R_L = 3 \Omega; T_j = 0 \div 125 \text{ }^\circ\text{C}$
		0.4			V	$V_D = V_{DRM}; R_L = 10 \text{ k}\Omega; T_j = 125 \text{ }^\circ\text{C}$
Peak gate current	$I_{GM}$		10		A	
Peak reverse gate voltage	$V_{RGM}$		5		V	
Peak gate power dissipation	$P_{GM}$		200		W	
Average gate power dissipation	$P_{G(AV)}$		5		W	

### Switching

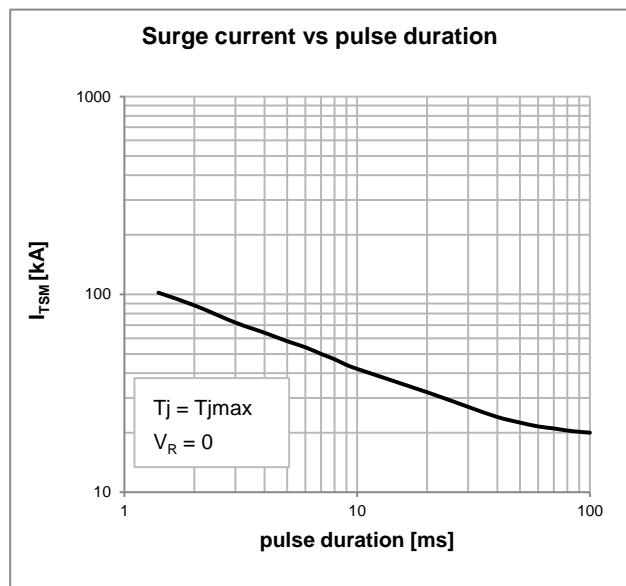
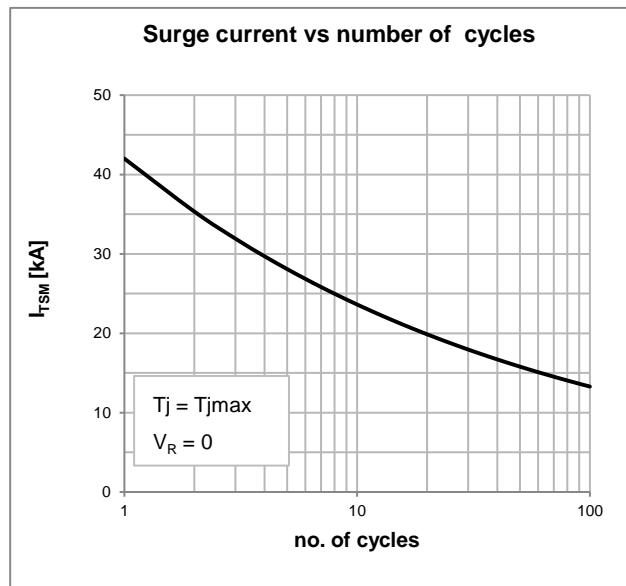
Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Critical rate of rise of on-state current	$di/dt$		250		A/ $\mu$ s	Switching from $V_{DRM} \leq 3000 \text{ V}$ - repetitive
Critical rate of rise of on-state voltage	$dv/dt$		1000		V/ $\mu$ s	Linear ramp up to 80% of $V_{DRM}$
Gate controlled delay time	$t_d$		4		$\mu$ s	$I_{TM} = 50 \text{ A}; V_D = 1500 \text{ V}; V_G = 20 \text{ V}$ $R_G = 20 \Omega; t_r = 0.1 \mu\text{s}; t_p = 20 \mu\text{s}$
Turn-off time	$t_q$		750		$\mu$ s	$I_{TM} = 2500 \text{ A}; di/dt = 25 \text{ A}/\mu\text{s}; V_R \geq 50 \text{ V}$ $dV/dt = 50 \text{ V}/\mu\text{s}$ linear to 80% $V_{DRM}$ $V_G = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$
Reverse recovery charge	$Q_{rr}$			7500	$\mu$ C	$I_T = 2000 \text{ A}$ $di/dt = 20 \text{ A}/\mu\text{s}$
Reverse recovery current	$I_{rr}$			180	A/ $\mu$ s	$V_R \geq 50 \text{ V}$ $T_j = T_{jmax}$

### Thermal and mechanical

Parameter	Symbol	Min	Max	Typ	Unit	Conditions
Operating temperature	$T_j$	-40	125		$^\circ\text{C}$	
Storage temperature	$T_{stg}$	-40	125		$^\circ\text{C}$	
Thermal resistance junction to case	$R_{th(j-c)}$		0.0065		$^\circ\text{C/W}$	Double side cooled , DC
Thermal resistance case to sink	$R_{th(c-s)}$		0.0015		$^\circ\text{C/W}$	Double side cooled, mounting surfaces smooth, flat and greased
Mounting force	$F$	60	70		kN	
Weight	$W$			1900	g	

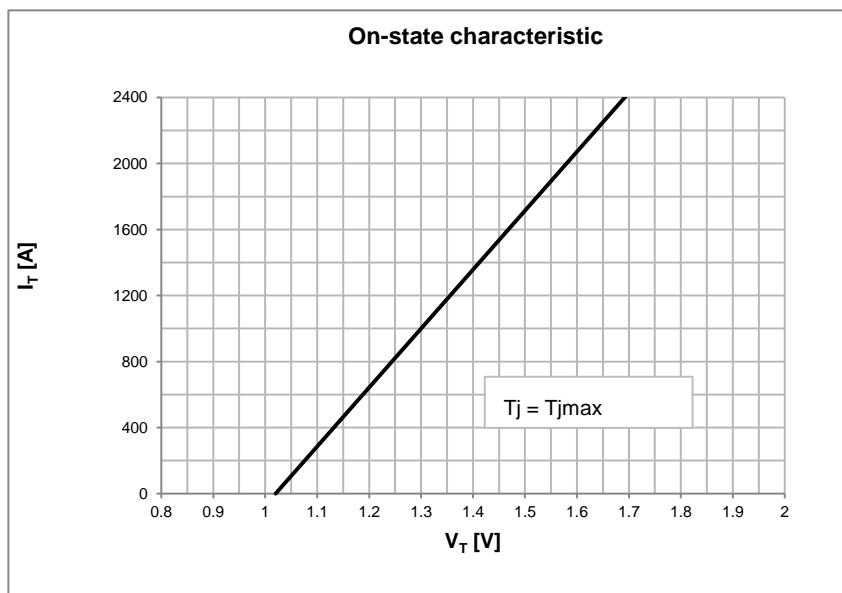
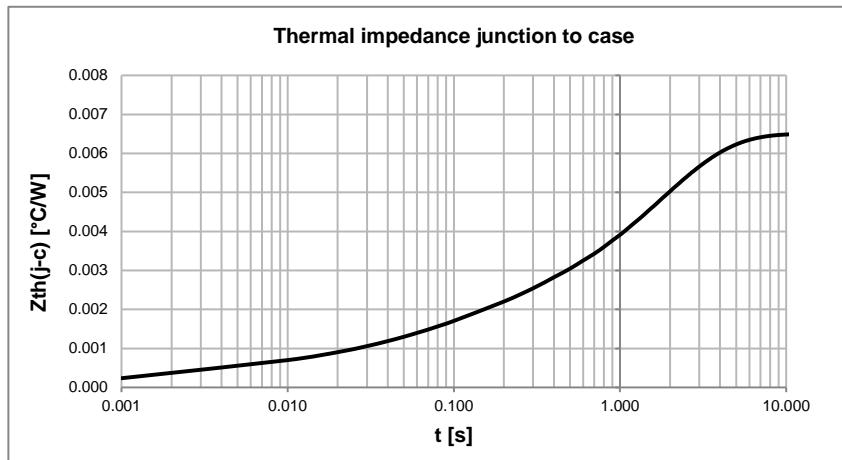
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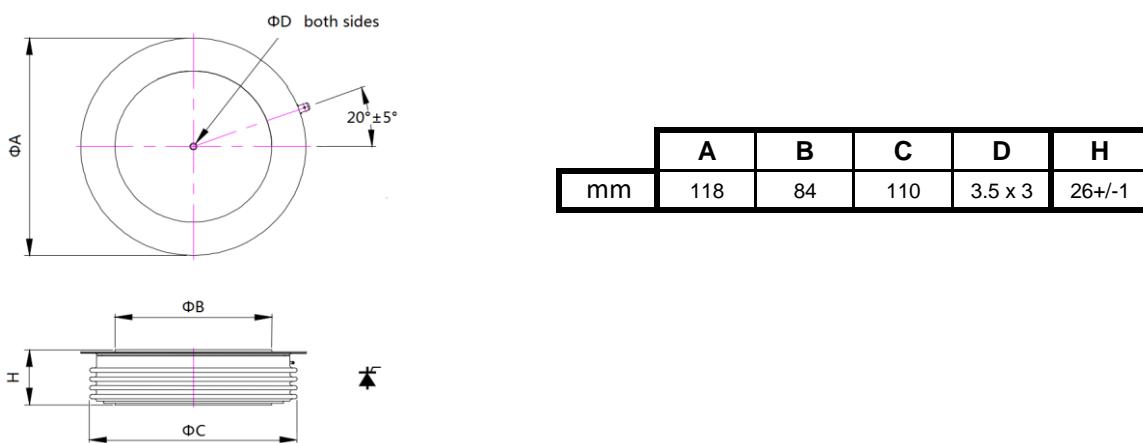


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## OUTLINE AND DIMENSIONS



- All the characteristics given in this data sheet are guaranteed only with uniform clamping force, cleaned and lubricated heatsink surfaces with flatness < 0.03 mm and roughness < 2µm